

# X-ray Photoelectron Spectroscopy XPS to characterize glassy materials



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**Photoelectric effect** presented by R. Hertz in 1887 and explained by A. Einstein in 1905



Nobel Price of Physic in 1921



#### **XPS or ESCA : Electron Spectroscopy for Chemical Analysis**

**Analytical tool** 

#### **Kai SIEGBAHN**



Nobel Price of Physic in 1981



#### Precision Method for Obtaining Absolute Values of Atomic Binding Energies

CARL NORDLING, EVELYN SOKOLOWSKI, AND KAI SIEGBAHN Department of Physics, University of Uppsala, Uppsala, Sweden (Received January 10, 1957)



## What is XPS ?



is characteristic of ONE orbital of ONE atom in ONE environment

164 162 160 158 156 154 152 150 148 146

XPS spectra are obtained by irradiating a material with a X-rays beam while simultaneously measuring the kinetic energy and number of electrons escaped from material.



#### Survey spectrum or Wide scan spectrum



#### **Electron intensity as a function of energy**

#### X-ray beam Anode-> Monochromator

The photoelectrons are:

- **Ejected** from the sample surface with an KE
- Focused and transferred by electromagnetic lenses
- Energy filtered by a analyser
- **Detected** and recorded by a counting system



# 1- What allows XPS ?

Surface analysis Atomic Identification Quantitative analysis Chemical analysis

2- Equipment



# **3- XPS to characterize glassy materials**



# 1- What allows XPS ?

#### Surface analysis

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# **3- XPS to characterize glassy materials**

# Surface analysis

Interaction process between photoelectrons and solid

3 steps :

- Absorption of the photon and creation of a photoelectron
- Transport of electrons to the surface | without inelastic scatter

II inelastic scatter

- III many inelastic scatter
- **Escape** of the electrons from surface to the vacuum





Surface analysis : depth analysis < 10nm



Not because of the photon beam penetration,

because of the electron escape without energy7loss

# Surface analysis

#### Inelastic mean free path ( $\lambda$ ) =

#### Average distance between successive inelastic collisions



Mean free path  $\lambda$  depends of:

- electrons kinetic energy
- chemical composition,
- structure and the density



63 % of all photoelectrons will come from within one  $\lambda$  of depth.

The majority of photoelectrons will come from 3λ.

#### Depth analysis : 5- 10nm



# 1- What allows XPS ?

Surface analysis

#### **Atomic Identification**

Quantitative analysis Chemical analysis

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**3- XPS to characterize glassy materials** 

### **Atomic Identification**

All the elements present in the compound are detected except H and He

Limit sensibility : around 0.1% (atomic percentage)

For each atom present in the surface, all the orbitals are ionized if :

 $E_b < hn$ 

H																	<sup>2</sup> He
3 Li	4 Be											5 B	°C	7 N	80	9 F	10 Ne
11 Na	12 Mg											13 AI	14 Si	15 P	16 S	17 CI	18 Ar
19 K	20 Ca	21 Sc	22 	23 V	24 Cr	25 Mn	26 Fe	27 Co	28 Ni	29 Cu	30 Zn	Ga Ga	32 Ge	33 As	34 Se	35 Br	36 Kr
37 Rb	38 Sr	39 Y	40 Zr	41 Nb	42 Mo	43 Tc	44 Ru	45 Rh	46 Pd	47 Ag	48 Cd	49 In	50 Sn	51 Sb	52 Te	53 	54 Xe
55 Cs	56 Ba	57 La	72 Hf	73 <b>Ta</b>	74 W	75 Re	76 Os	77 Ir	78 Pt	79 Au	80 Hg	81 TI	82 Pb	83 Bi	84 Po	85 At	86 Rn
87 Fr	Ra Ra	89 Ac	104 Rf	105 Db	106 Sg	107 Bh	108 Hs	109 Mt	110 Ds	111 Rg	112 Cn	113 Uut	114 FI	115 Uup	116 Lv	117 Uus	118 Uuo
<sup>6</sup> 58 59 60 61 62 63 64 65 66 67 68 69 70 71																	
			Ce	Pr	Nd	Pm	Sm	Eu	Gd	Tb	Dy	Ho	Er	Tm	Yb	Lu	
			Th	Pa	U	Np	Pu	Am	Cm	Bk	Cf	Es	Fm	Md	No	Lr	

#### ΑΙ Κα A survey spectrum allows the atoms identification: hn = 1486,6 eV Valence band **Core peaks** Valence band (30 to 0eV) (1300 to 30eV) **e**<sup>-</sup> 2p<sup>6</sup> 2s<sup>2</sup> Core peaks **e**<sup>-</sup> $1s^2$ **e**<sup>-</sup> 1000 800 600 400 200 1200 0 10 Binding energy (eV)

### **Atomic Identification**

#### Valence band

#### **Experimental visualisation of density of states DOS**

- highest occupied electronic level (0 à 30eV)
- characteristic of bonds

The intensity are then modulated by photoionization cross-section to be compared to the valence spectra

$$DOS_{total modulated} = \sum_{A,o} \sigma_{A,o} * DOS_{A,o}$$
 (E)

Al Kα hn = 1486,6 eV



#### Theoretical calculations allow to simulate DOS



E<sub>b</sub> Binding energy

#### **Atomic Identification – Core peaks**



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### **Atomic Identification – Core peaks**



Survey spectrum SiO<sub>2</sub>

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## **Atomic Identification – Core peaks**

#### The binding energies (eV) are tabulated like in this exemple:



# **Core Peak : shapes and denomination**

For s orbital, one peak is observed :



For p, d, f orbitals, **two peaks** are observed :



The separation between the two peaks are named **spin orbital splitting**.

This splitting is due to the combination between two characteristics of the photoionized electron:

- its angular momentum I (velocity and radius of the orbit)
- its spin momentum s

#### **Spin-orbit coupling**



Depending on the electron movement compared to the orbital movement

## **Core Peak : shapes and denomination**



**2s** 



**2**p<sub>3/2-1/2</sub>









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# **3- XPS to characterize glassy materials**

### **Quantitative analysis**



Depends on

- Spectrometer characteristics
- Sample: element concentration,
   photoemission cross section ...

#### The quantification is obtained in atomic percentage, and is not an absolute quantification

Modulated by Photoionisation cross section  $\sigma_{eff}$  or Relative Sensitivity Factors (RSFs)

Journal of Electron Spectroscopy and Related Phenomena, 8 (1976) 129–137 © Elsevier Scientific Publishing Company, Amsterdam – Printed in The Netherlands



J. H. SCOFIELD

Lawrence Livermore Laboratory, University of California, Livermore, California 94550 (U.S.A.) (First received 27 June 1975; in final form 20 August 1975)

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	Tabl	e 2.	Photoion:	ization d	ross sect	tions at 1	487 eV in	units o	f the C 1:	s cross se	ction of	13,600 bi	arns.
		Z	Total	181/2	281/2	2p1/2	2p3/2	301/2	3p1/2	3p3/2	3d3/2	3d5/2	4a1/2
	н	1	0.0002	0.0002									
	He	2	0.0082	0.0082									
Journal of Electron Spectroscopy and Related Phenomena, 8 (1976) 129–137	Li	3	0.0576	0.0568	0.0008								
© Elsevier Scientific Fublishing Company, Ansierdam ~ Printed in The Netherlands	Be	4	0.202	0.1947	0.0072								
	в	2	0.508	0.486	0.0220	0.0001	0.0001						
	5	0	1.05	1.000	0.04/7	0.0005	0.0010						
HARTREE-SLATER SUBSHELL PHOTOIONIZATION CROSS-SECTIONS			2.09	2.00	0.0007	0.0022	0.0043						
AT 1254 AND 1487 eV	ř	č	1 68	1 43	0 210	0.0161	0.0217						
	Ne	10	6.70	6.30	0.296	0 0347	0.0683						
			0.70	0.90	0.290	0.0347	0.0005						
	Na	11	9.14	8.52	0.422	0.0654	0.1287	0.0064					
J. H. SCOFIELD	Mg	12	12.11	11.18	0.575	0.1125	0.221	0.0285					
Lawrence Livermore Laboratory, University of California, Livermore, California 94550 (U.S.A.)	Al	13	1.35	,	0.753	0.1811	0.356	0.0535	0.0011	0.0022			
(First received 27 June 1975; in final form 20 August 1975)	Si	14	1.87		0.955	0.276	0.541	0.0808	0.0047	0.0093			
	P	15	2.52		1.18	0.403	0.789	0.1116	0.0124	0.0244			
	5	16	3.33		1.43	0.567	1.11	0.1465	0.0262	0.0512			
	C1	17	4.31		1.69	0.775	1.51	0.1852	0.0486	0.0947			
	Ar	18	5.49		1.97	1.03	2.01	0.227	0.0821	0.1597			
	ĸ	19	6.90		2.27	1.35	2.62	0.286	0.1229	0.239			0.0069
	Ca	20	8.55		2.59	1.72	3.35	0.351	0.1720	0.335			0.0268
	Sc	21	10.39		2.91	2.17	4.21	0.411	0.221	0.429	0.0017	0.0025	0.0314
	Ti	22	12.48		3.24	2.69	5.22	0.473	0.276	0.537	0.0055	0.0081	0.0355
	¥	23	14.84		3.57	3.29	6.37	0.538	0.339	0.657	0.0125	0.0184	0.0394
	Ċr	24	17.43		3.91	3.98	7.69	0.596	0.400	0.773	0.0264	0.0387	0.0161
	Mn	25	20.39		4.23	4.74	9.17	0.674	0.485	0.938	0.0424	0.0622	0.046415
	Fe	26	23.61		4.57	5.60	10.82	0.745	0.569	1.10	0.0694	0.1017	0.0497
	Co	27	27.10		4.88	6.54	12.62	0.818	0.660	1.27	0.1082	0.1582	0.0529

## **Quantitative analysis**



Use of **Relative Sensitivity Factors (RSFs)** to convert the recorded signal to a corrected intensity for use in a **quantification calculation** 



# 1- What allows XPS ?

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# **3- XPS to characterize glassy materials**

### **Core peaks: Binding energy value and shift**



Perkin Elmer Edition

oxydation number, variation in chemical environment, bonds,<sup>22</sup>...

## **Core peaks : acquisition**



#### **Energy resolution depends on Analyzer Pass Energy**

The **pass energy** translates the potential difference between inner and outer hemisphere of the analyzer



Carbon is present. But what is its environment?



# **Core peaks : binding energy calibration**



**Conducting sample** in electrical contact with the spectrometer  $\rightarrow$  Fermi level equalization

Binding energy calculation: The measured kinetic energy of the photoelectron is influenced by :

- the work function of the sample:  $\Phi_{s}$
- the work function of the instrument :  $\Phi_i$

Internal reference is needed for calibration of all the binding energies of the sample:

Exemples : C1s: 285.0 eV Au4f<sub>7/2</sub>: 84.0 eV

## **Chemical characterisation – Binding energy shifts**



In the bond, the Si valence electrons are attracted by the Oxygen atoms. The oxydation state of the silicium atoms change Si<sup>0</sup>  $\rightarrow$  Si<sup>4+</sup>.

The remaining Si valence electrons are more attracted by the positive charge of the nucleus, the binding energy is then increasing in the Si-O bond compare to Si neutral.

# **Chemical characterisation – Binding energy shifts**

#### Change of neighbour characteristic



Electronic distribution around the Ti nucleus  $\neq$  in TiS<sub>2</sub> and TiO<sub>2</sub>, even if the titanium is referenced in the oxydation number Ti<sup>4+</sup> in both cases.

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**Oxygen is more electronegative then sulfur**, then the **Ti-O bonds is more ionic then Ti-S bonds**. When the electronegativity of the ligand increases, the nucleus feels a depletion in electrons. The remaining electrons are then more attracted by the positive field of the nucleus.

## **Chemical characterisation – Binding energy shifts**



The binding energy of the C1s peak is changing, depending on the attractivity of the ligand on the carbon electronic cloud.

#### **Chemical characterisation – Other probes**

When chemical shift of the principal core peak is not large enough

 $\rightarrow$  other probes are useful.

"Shake up" satellites

**Multiplet splitting** 

**Auger peaks** 

Valence spectra

#### **Chemical characterization - Peaks and satellites**



The position and intensity of the satellite can help to elucidate the oxydation degree of the atom.

Energie de liaison (eV)

satellite

Energie de liaison (eV)

### **Chemical characterization - Peaks and satellites**

"Multiplet" Structures / Multiplet splitting

For system with unpaired electrons in valence levels **several final states** 



### **Chemical characterization - Peaks and satellites**

**Multiplet splitting** 



The shape of the peak with or without multiplet splitting can give informations on the electronic valence organization

#### **Chemical characterization – Auger peaks**

#### **Relaxation phenomena – Auger process or X-ray fluorescence**





A : photoionisation (A +  $hv_1 \rightarrow A^+ + e^-$ ) Emission of an XPS core electron => core peak

Relative propability of Auger emission and Xray emission depending on the atomic number of atom

- B: desexcitation through Auger effects  $(A^+ \rightarrow A^{++} + e^-)$ Emission of an Auger electron named:  $KL_1L_{2,3} =>$  Auger peak
- C : desexcitation through fluorescence X ( $A^+ \rightarrow A^+ + hv_2$ )

XPS peaks: E<sub>b</sub> independant from hv Auger peaks: E<sub>c</sub> independant from hv

### **Chemical characterization – Auger peaks**



#### **Chemical characterisation - Valence spectra**





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# **3- XPS to characterize glassy materials**

Kratos – Axis Ultra



#### THERMO SCIENTIFIC - Escalab 250Xi



#### THERMO SCIENTIFIC – K-Alpha



All our spectrometer are directly connected to a glove box in Ar atmosphere



Vacuum system : many pumps to have an ultra high vacuum in any parts of the system (~10<sup>-9</sup>mbar)



Hemispherical analyzer

The photoelectrons are:

- Ejected from the sample surface with an KE
- Focused and transferred by electromagnetic lenses
- Energy filtered by a analyser
- **Detected** and recorded by a counting system

Sample preparation – necessity to have a very clean surface

Very sensitive to extreme surface, top atomic layers



#### Sample Types/ Samples holders

# Capable to analyse samples from different nature without any preparation

#### Solids

- Bulk, thin films, powders, fibers
- Crystallized, amorphous, compact or porous
- Insulating, semiconducting, conducting
- Stable in the UHV chamber

#### "Cold Analysis" thanks to liquid nitrogen

For materials sensitive to Xray irradiation, or to frooze Gel / Liquids

#### Surface cleaning

Frozen liquid



Maintained on the stub or bar with:

- double-sided adhesive tape
- clips



Sputter ion sources In-vacuum fracture Cross section polisher

# **XPS spectrometer - Charge compensation**

#### Why?

Photoemission from an insulating material leads to the build-up of a positive charge (insulators cannot dissipate charge generated by photoemission process.)

Analysis insulators in XPS presents problems:

- Spectral peaks are distorted : difficult to **distinguish an artefact from a shift** in energy due to the sample chemistry.
- Apparition of peaks without meaning
- No signal or very shifted

#### How can we compensate?

An external source of low-energy electrons is required in the form of an electron « flood gun », to replace emitted electrons





Photoemitted electrons leave local positive charges on the surface

#### **XPS spectrometer – Change depth analysis**

**Destructive method: Ion etching** 

Ion mode: monoatomic argon Ar<sup>+</sup>, argon cluster mode Ar<sub>n</sub><sup>+</sup>

To obtain concentration profile on depth more than 10 nm

Sputtering the surface within the spectrometer and use normal mode of XPS (record spectra)



#### **XPS spectrometer – Change depth analysis**

Non-destructive method: Variation of analysis angle ARXPS (Angle Resolved XPS)



Analysis depth as a function of detection angle



After tilt  $\rightarrow$  exaltation of extreme surface signal : SiO<sub>2</sub>  $\checkmark$  and Si

#### **XPS spectrometer – Change depth analysis**

Non-destructive method: Use of another Xray energy

Possible even in lab with Ag-L $\alpha \rightarrow h\nu$ =2950.6eV







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# **3- XPS to characterize glassy materials**

#### XPS is sensitive to

short range order, local struture, chemical environment of atoms, electronic distribution ...

Compare to a cristal, a glass doesn't have organization at long range order, and a kind of disorder in bond length, angle values ...

But a glass has well defined short range order and mid-range order (nearest neighbours)

#### So XPS is a perfectly suitable tool to characterize

glassy materials as well as cristals

In glass, disorder exists in bond length, angle...



Widening of the peaks compare to the crystal

Former GeS<sub>2</sub> : covalent bonds Modifier Na<sub>2</sub>S : ionic bonds



The electronic density around the sulfur is totally different in these two materials because of the bond nature, which is very well translated thanks to the sulfur peak S2p.

Sulfur atoms are more negative in Na<sub>2</sub>S, their peak S2p has a lower binding energy compare to GeS<sub>2</sub>.

#### Influence of the amount of modifier:

Classical scheme for addition of modifier in formar glass

 $Na_2S + GeS_2$ 



Coexistence of Bridging sulfur: S<sub>b</sub> and Non-bridging sulfur: S<sub>nb</sub>

xNa<sub>2</sub>S-(1-x)GeS<sub>2</sub>





In xNa<sub>2</sub>S-(1-x)GeS<sub>2</sub>, two different environments for sulfur are present. Thanks to the sulfur peak S2p evolution, depending on the **amount of modifier** : - Evidence of **the evolution of proportion of the two kinds of atom sulfur**.

- Change in the position than in the negative character of sulfur of the two kinds of atom sulfur

#### Influence of the nature of the modifier cation (x=0.5):





Coexistence of S<sub>b</sub> and S<sub>nb</sub>

Depending on the nature of the modifier cation, we can observe:

- A binding energy for both bridging and non-bridging sulfurs higher for Ag
- ➤ A difference of binding energy between Sb and Snb less important for Ag Δ (E<sub>b</sub>S<sub>b</sub> - E<sub>b</sub>S<sub>nb</sub>)



#### Influence of the nature of the modifier cation:

**Theoretical calculations** allow to reach the Mulliken population, informing on the electron population on each atom. The following results were obtained for the charges on bridging  $(q_{sb})$  and non-bridging  $(q_{snb})$  sulfurs:

Mulliken population										
N	a <sub>2</sub> GeS <sub>3</sub>	eS <sub>3</sub> -0,64 to -0,70 -0,86 to -0		,87	Negative characte	er higher for <mark>Snb</mark> compare to <b>Sb</b>				
Li	2GeS3	-0,63 to -0,69	-0,82 to -0,84		Negative characte	er higher for <b>Na and Li, compared</b>				
A	g2GeS3	-0,62 to -0,66	-0,72 to -0	,74	to Ag, especially	for non-bridging sulfurs				
		(	(							
		Mulliken p	opulation	XF	PS results S2p peaks					
		∆ (q <b>Sb</b> -	q <b>Snb)</b>	4	$\Delta$ (E <sub>b</sub> Sb - E <sub>b</sub> Snb)	_				
Na <sub>2</sub> GeS <sub>3</sub>		3 <b>0.20</b>	)eV		0.8eV					
Li <sub>2</sub> GeS <sub>3</sub>		0.17	'eV		0.9eV					
Ag <sub>2</sub> GeS <sub>3</sub>		3 0.09	eV		0.5eV					

XPS shows the importance of the nature of cation modifier on the electronic structure of the glasses.

The interactions between the orbitals of the cations and sulfurs are higher in  $Ag_2GeS_3$  compare to  $Na_2GeS_3$  or  $Li_2GeS_3$ .

Captors Cu<sub>10</sub>(As<sub>0,4</sub>S<sub>0,6</sub>)<sub>90</sub> : mesures potentiométriques



Decrease of the performances after hours of use. After 166h, no more answer of the system. Why ? Vhy Sanalyses to understand the ageing process



#### Captors Cu<sub>10</sub>(As<sub>0,4</sub>S<sub>0,6</sub>)<sub>90</sub> : mesures potentiométriques



Decrease of the performances after hours of use. After 166h, no more answer of the system. Why ? XPS analyses to understand the ageing process

 $\begin{array}{c}
45 \\
43 \\
& 41 \\
39 \\
37 \\
35 \\
0 \\
5 \\
10 \\
15 \\
20 \\
25 \\
Time in solution (h)
\end{array}$ 



Beside the observed modification of chemical environements,

➡ evolution of the surface composition

Ageing process linked to apparition of modified surface layer

## **XPS to characterize materials**



**Ti<sup>4+</sup>** in mixed  $S_2^{2-/}S^{2-}$  environment : 294,9eV

Ti<sup>4+</sup> in S<sup>2-</sup> environment : 295,7eV

#### **Energy storage : Li-ion battery**



During **charge** : Li are leaving from the cathode

 $\rightarrow$  oxydation reactions in cathode material

During discharge : Li are inserted in the cathode

 $\rightarrow$  reduction reactions in cathode material

**XPS : which redox processes allow the Li-intercalation ?** 

# **XPS to characterize materials**

#### Electrochemical cycling - $TiS_3$ is the negative electrode



#### **During the Li-insertion**

- the reduction occurs on the anion centers
- the Ti atoms are not the place of reduction in discharge
- $\succ$  the electronic distribution along the Ti-S bond is modified : value of  $\Delta$ (Ti-S<sup>2-</sup>)

**During the Li-deinsertion** > Reversibility of the redox process

## Conclusion

As a reminder, X-ray photoelectron spectroscopy technique allows:

Surface analysis (5-10nm)

**Detection of all elements except H and He** 

**Quantitative analysis** 

Qualitative analysis to highlight chemical environment and electronic structure because sensitive to

Oxydation degree short range order, local struture, chemical environment of atoms, electronic distribution ...



# Thank you for your attention



